

II. Schottky Rectifier

1.0A Surface Mount Schottky Rectifier

FM102~FM110

(Package: SOD-123)

<p>FEATURES</p> <ul style="list-style-type: none"> • Silicon epitaxial planar chip, metal-silicon junction • Batch process design, excellent power dissipation offers better reverse leakage current and thermal resistance • Ultra high speed switching • Low power loss, high efficiency • Low forward voltage drop, high current capability • Guardring for overvoltage protection • The plastic material carries UL recognition 94V-0 <p>MECHANICAL DATA</p> <ul style="list-style-type: none"> • Case : Molded plastic, SOD-123 / Mini SMA • Terminals : Plated terminals, solderable per MIL-STD-750, Method 2026 • Mounting position : Any • Polarity : Color band denotes cathode • Weight : approx. 0.027 grams 	<p>The diagram shows two views of the SOD-123 package. The top view is a rectangular case with a central black bar and dimensions: width 0.154(3.9) to 0.138(3.5), height 0.071(1.8) to 0.055(1.4), and thickness 0.012(0.3) Typ. The side view shows the lead profile with dimensions: lead width 0.122(2.8) to 0.096(2.4), lead height 0.067(1.7) to 0.051(1.3), lead thickness 0.035(0.9) Typ, and overall height 0.035(0.9) Typ.</p> <p>Case: SOD-123 Dimensions in inches and (millimeters)</p>
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Ratings & Electrical Characteristics

Ratings at 25° ambient temperature unless otherwise specified.

Single phase half-wave 60 Hz, resistive or inductive load, for capacitive load current derate by 20%.

Characteristics	Symbol	FM102	FM103	FM104	FM105	FM106	FM108	FM110	Units				
Component Marking		12	13	14	15	16	18	110					
Maximum recurrent peak reverse voltage	V _{RRM}	20	30	40	50	60	80	100	Volts				
Maximum RMS voltage	V _{RMS}	14	21	28	35	42	56	70	Volts				
Maximum DC blocking voltage	V _{DC}	20	30	40	50	60	80	100	Volts				
Maximum average forward rectified current See Fig.1	I _o	1.0							Amps				
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load. (JEDEC Method)	I _{FSM}	30							Amps				
Maximum forward voltage at 1.0 A DC	V _F	0.50		0.70		0.85			Volts				
Maximum DC reverse current @Ta = 25° at rated DC blocking voltage @Ta = 125°	I _R	0.5 10							mA				
Typical junction capacitance (Note 1)	C _j	120							PF				
Typical thermal resistance (Note 2)	R _{th-JA}	98							/W				
Operating temperature range	T _j	-55 to +125			-55 to +150								
Storage temperature range	T _{stg}	-65 to +175											

Notes:

1. Measured at 1.0 MHz and applied reverse voltage of 4.0V DC.
2. Thermal resistance junction to ambient.

F.E.C. Semiconductor

Ratings and Characteristic Curves of FM102~FM110

FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

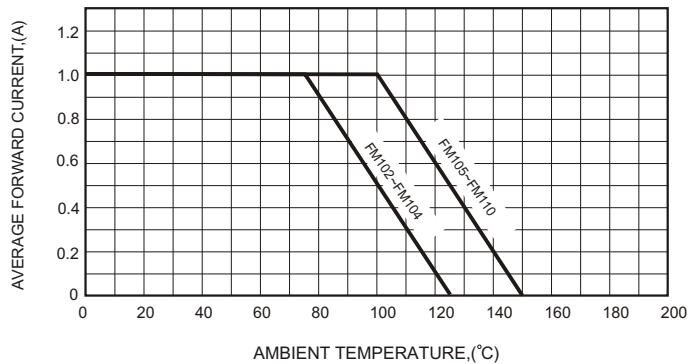


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

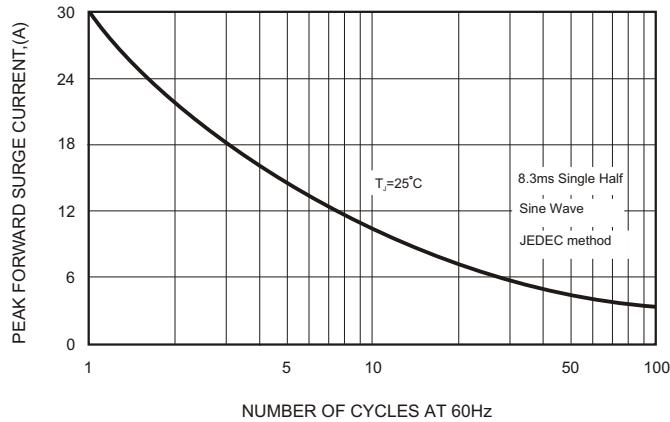


FIG.4-TYPICAL JUNCTION CAPACITANCE

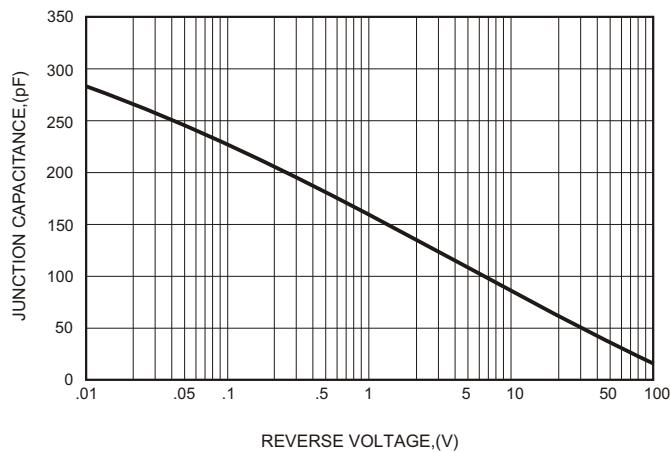


FIG.2-TYPICAL FORWARD CHARACTERISTICS

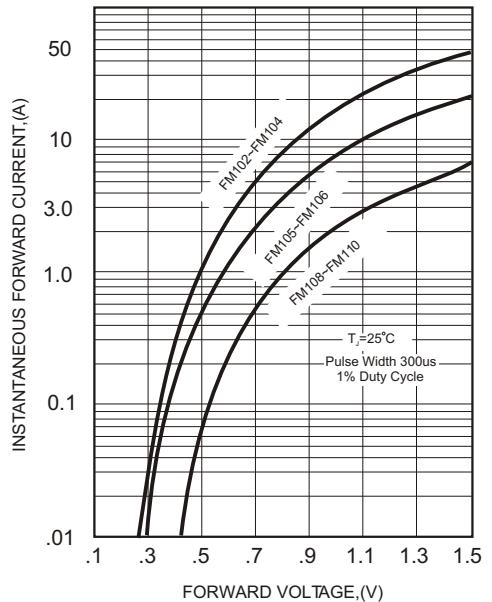


FIG.5 - TYPICAL REVERSE CHARACTERISTICS

